## **SanRex**®

### **TRIAC**

### **TMG40C60J**

 $I_{T(RMS)} = 40A, V_{DRM} = 600V$ 

SanRex Triac TMG40C60J is designed for full wave AC control applications. It can be used as an ON/OFF function or for phase control operation. TMG40C60J has an isolated diffusion type die with glass-passivated junctions. It achieves very high reliability and keeping stable design criteria.

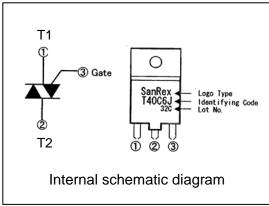
#### **Features**

- \* Glass-passivated junctions features
- \* High surge Current
- \* Low voltage drop
- \* Lead-free solder plated terminals
- \* UL registered E76102

### **Typical Applications**

- \* Home Appliances
- \* Heater Controls
- \* Lighting Controls
- \* Temperature Controls





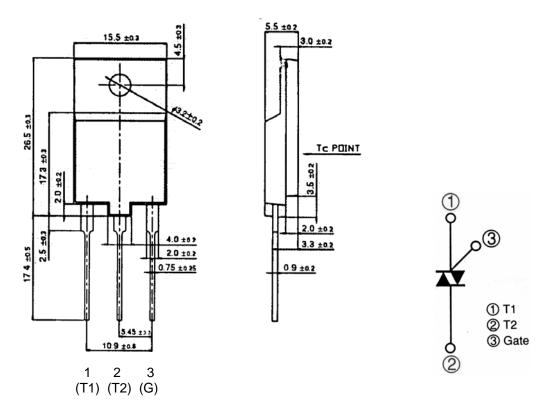
< Maximun	n Ratings>	(Tj = 25°C unless otherwise noted)		
Symbol	Item	Conditions	Ratings	Unit
$V_{DRM}$	Repetitive Peak Off-state Voltage		600	V
I <sub>T(RMS)</sub>	R.M.S. On-state Current	T <sub>C</sub> = 73°C	40	Α
I <sub>TSM</sub>	Surge On-state Current	One cycle, 60Hz, Peak, non-repetitive	420	Α
l²t	I <sup>2</sup> t (for fusing)	Value for one cycle surge current	730	A <sup>2</sup> s
P <sub>GM</sub>	Peak Gate Power Dissipation		10	W
P <sub>G(AV)</sub>	Average Gate Power Dissipation		1	W
I <sub>GM</sub>	Peak Gate Current		3	Α
V <sub>G M</sub>	Peak Gate Voltage		10	V
Viso	Isolation Voltage	A.C. 1 minuite	1500	V
Tj	Operation Junction Temperature		-40 to +125	°C
Tstg	Storage Temperature		-40 to +150	°C
	Mass	Typical Value	5.6	g

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TRIAC TMG40C60J

< Electrical Characteristics >

	t .	0 100	Ratings				
Symbol	Item		Conditions	Min.	Тур.	Max.	Unit
I <sub>DRM</sub>	Repetitive Peak Off-state Current		$T_j = 125$ °C, $V_D = V_{DRM}$ , Single Phase, Half wave			5	mA
$V_{TM}$	Peak On-State Voltage		I <sub>T</sub> =60A, Instant measurement			1.4	V
I <sub>GT</sub> 1 <sup>+</sup>	QI	- Gate Trigger Current	$V_D = 6V$ , $I_T = 1A$			50	mA
I <sub>GT</sub> 1	QII					50	mA
I <sub>GT</sub> 3 <sup>+</sup>	QIV					-	mA
I <sub>GT</sub> 3	QIII					50	mA
$V_{GT}1^{+}$	QI	Gate Trigger Voltage	$V_D = 6V$ , $I_T = 1A$			1.5	V
V <sub>G T</sub> 1	QII					1.5	V
$V_{GT}3^{+}$	QIV					-	V
V <sub>G</sub> <sub>T</sub> 3 <sup>-</sup>	QIII					1.5	V
$V_{GD}$	Non-Trigger Gate Voltage		$Tj = 125^{\circ}C, V_{D}=1/2V_{DRM}$	0.2			V
(dv/dt)c	Critical Rate of Rise of Commutation Voltage		$Tj = 125^{\circ}C$ , $V_D=2/3V_{DRM}$ , $(di/dt)c=-20A/ms$	10			V/Fs
ΙH	Holding Current				30		mA
Rth(j-c)	Thermal Resistance		Junction to case			1.1	°C/W



<sup>\*</sup> Dimensions in millimeters (1mm=0.0394")